

# Nitrogen and fluorine doped $\text{ZrO}_2$ : A promising $p$ - $n$ junction for ultraviolet light-emitting diode

Sudhir K. Pandey ‡

UGC-DAE Consortium for Scientific Research, University Campus, Khandwa Road, Indore - 452001, India

School of Engineering, Indian Institute of Technology Mandi, Mandi - 175001, India

**Abstract.** In the present work we study the effect of nitrogen (N) and fluorine (F) doping in the electronic properties of  $\text{ZrO}_2$  by using *ab initio* electronic structure calculations. Our calculations show the importance of on-site Coulomb correlation in estimating the correct band gap of  $\text{ZrO}_2$ . The N and F doping provide hole and electron type impurity states in the band gap closer to the top of the valance band and bottom of the conduction band, respectively. The formation of such impurity states may be exploited in fabricating a  $p$ - $n$  junction expected to be useful in making an ultraviolet light-emitting diode.

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‡ Electronic mail: sk\_iuc@rediffmail.com

## 1. Introduction

The doping of N in place of oxygen (O) in the technologically important oxide semiconductors has attracted a great deal of attention from last couple of years [1, 2, 3, 4, 5, 6, 7, 8]. Most of these activities is directed towards the creation of magnetism by non-magnetic doping in the conventional dilute magnetic semiconducting materials like TiO<sub>2</sub>, ZnO, MgO, *etc.* [5, 6, 7, 8]. It has been shown that the doping N at O sites is equivalent to creating holes in these systems. Recently, we have shown that F doping in TiO<sub>2</sub> is equivalent to electron doping in it [5]. Thus one expects that N- and F-doped oxide semiconductors may be useful in fabricating many technologically important materials where *p*- and *n*-type conduction are to be exploited.

Here we explore such possibility in a technologically important wide band gap semiconductor viz. ZrO<sub>2</sub> [9, 10, 11]. At room temperature it shows monoclinic structure and it converts into tetragonal and cubic structures with increasing temperature. The compound is a direct band gap semiconductor and its band gap reported to vary from 5 to 7 eV depending upon the structural phases and experimental methods used in extracting it [12, 13, 14]. It is a crucial refractory material used in insulation, abrasive, enamel, *etc.* It is also an important high k-dielectric compound predicted to be used as a gate dielectric material [15, 16].

In this work we study the modification of electronic structure of monoclinic ZrO<sub>2</sub> when N and F are doped at O sites by using supercell method of *ab initio* electronic structure calculations. The on-site Coulomb interaction is found to be important in getting the correct band of the compound. The N- and F-doped TiO<sub>2</sub> are found to be *p*- and *n*-type semiconductors, respectively. It is proposed that these semiconductors may be useful in fabricating a *p-n* junction which can be used as an efficient ultraviolet (UV) light-emitting diode (LED).

## 2. Computational details

The spin unpolarized electronic structure calculations of ZrO<sub>2-x</sub>N<sub>x</sub> and ZrO<sub>2-x</sub>F<sub>x</sub> (x=0, 1/32, 1/16 and 1/8) compounds have been carried out by using *state-of-the-art* full-potential linearized augmented plane wave (FP-LAPW) method [17]. The lattice parameters used in the calculations are taken from the literature [18, 19] which are corresponding to monoclinic and tetragonal structure. Here one should keep in mind that on general ground lattice parameters are expected to change with doping. However, on comparing the ionic radii of N and F with O one expects only small change in the lattice parameters which have little effect on the electronic properties of the compounds studied in present work. Moreover, any such attempts of computing lattice parameters using Elk code is very time consuming as one needs to carry out different calculations by varying four parameters viz. a, b, c and angle beta. The geometry optimization for ZrO<sub>2</sub> was carried out until the total magnitude of force at each atomic site comes out to be less than 13 meV/Bohr. The muffin-tin sphere radii were chosen to be 2 Bohr for

the Ti atom and 1.6 Bohr for the N, O, and F atoms. The 48, 24 and 12 atoms per cell were considered for calculating the self-consistent charge densities of  $x=1/32$ ,  $1/16$  and  $1/8$  compounds, respectively.

For the exchange correlation functional, we have considered recently developed generalized gradient approximation (GGA) form of Perdew *et al.* [20]. Here it is important to note that local density approximation (LDA) and GGA based results often underestimates the band gap of semiconductors and insulators [21]. In order to find the correct band gap one can use various improved methods like GW approximation, DFT+ $U$  and hybrid functional. These methods are also found to be useful in studying the electronic structure of many doped semiconductors [22, 23, 24]. In the DFT+ $U$  method one needs the value of  $U$  for a particular set of orbitals, whereas in the other two methods such restriction is relaxed. However, among these methods DFT+ $U$  is simple and computationally less demanding. Thus we use DFT+ $U$  method to study the band gap problem of ZrO<sub>2</sub>. The effect of on-site Coulomb interaction among O  $2p$  and Zr  $4d$  electrons are considered within GGA+ $U$  formulation of the DFT [25]. The value of  $U$  is varied from 1 to 4 eV. The self-consistent solutions were obtained by considering 27 k-points in the irreducible part of the Brillouin zone. The self-consistency was achieved by demanding the convergence of the total energy to be smaller than  $10^{-4}$  Hartree/cell.

### 3. Results and discussions

As mentioned above, the ground state structure of ZrO<sub>2</sub> is experimentally found to be monoclinic (space group  $P21/c$ ) and it shows structural transition from monoclinic to tetragonal (space group  $P42/nmc$ ) above room temperature. The total energy calculations of ZrO<sub>2</sub> in monoclinic and tetragonal phases also suggest that the monoclinic structure is a true ground state as its energy is found to be  $\sim 170$  meV less than that of tetragonal structure. In the monoclinic phase each unit cell contains one kind of Zr atoms and two kinds of O atoms (O1 and O2) occupying the  $4e$  Wyckoff positions. Therefore, each unit cell contains 4 Zr atoms and 8 O atoms and every Zr atom is surrounded by 7 O atoms. The atomic positions of Zr, O1 and O2 atoms after geometry optimization are found to be ( 0.2743, 0.0433, 0.2091), (0.0648, 0.3248, 0.3512) and (0.4493, 0.7558, 0.4676), respectively, which are slightly different from the experimentally obtained values of (0.2758, 0.0404, 0.2089), (0.069, 0.342, 0.345) and (0.451, 0.758, 0.479) for Zr, O1 and O2 atoms, respectively [18].

The total density of states (TDOS) and partial density of states (PDOS) of ZrO<sub>2</sub> compound are plotted in Fig. 1. The insulating ground state for ZrO<sub>2</sub> compound is clearly evident from Fig. 1(a) where one can see a large band gap of 4 eV. The valance band (VB) and conduction band (CB) are predominantly consisting of O  $2p$  and Zr  $4d$  states, respectively as seen from Fig. 1(b). One can also observe small contributions of Zr  $4d$  and O  $2p$  PDOS in VB and CB, respectively. Under pure ionic model for the compound one would not have expected the presence of Zr  $4d$  and O  $2p$  states in the VB and CB. This behaviour may be considered as a signature for breakdown of pure ionic

character of Zr-O bonds. Although our calculated band gap of 4 eV is  $\sim 1$  eV less than the experimental one [13], however it provides fairly better estimate of the band gap in comparison to earlier calculated LDA based gaps of 3.35 eV [26] and 3.58 eV [14]. Here one should keep in mind that the GGA is a better approximation than LDA and use of GGA is expected to improve the gap. Moreover, FP-LAPW method used in the present work was found to provide better estimate of the gap in comparison to other methods [27]. Thus the use of GGA within FP-LAPW method could be the possible reason for better estimate of band gap in the present work.

The correct band gap of ZrO<sub>2</sub> are obtained by carrying out GGA+ $U$  calculations where we consider different values of  $U$  for Zr  $4d$  and O  $2p$  electrons. The use of  $U$  for these two orbitals can be justified by looking at the PDOS shown in Fig. 1(b) where we have seen the presence of O  $2p$  and Zr  $4d$  states in the valence band as well as in the conduction band. The  $U$  dependent band gap of the compound is shown in the inset of Fig. 1(a). It is evident from the inset that the band gap monotonically increases with increasing  $U$  and  $U \approx 3.5$  eV provides a correct band gap of 5 eV. This value of  $U$  is a reasonable estimate for  $4d$  and  $2p$  electrons and closer to those values of  $U$  which are found to provide fairly good electronic and magnetic properties of MgO and Sr<sub>3</sub>NiRhO<sub>6</sub> ( $3d$  and  $4d$  electrons system) compounds [6, 28].

The energy of monoclinic Zr<sub>4</sub>O<sub>7</sub>N is found to be  $\sim 448$  meV less than that of tetragonal Zr<sub>4</sub>O<sub>7</sub>N. On comparing this energy difference with that of ZrO<sub>2</sub> one can say that the N-doping is giving more stability to the monoclinic structure. This suggests that the monoclinic structure is a true ground state structure for the N-doped compounds studied here. N doping at O site changes the electronic structure of the compound drastically and N-doped ZrO<sub>2</sub> becomes metallic as evident from Fig. 2(a)-1(c). The N  $2p$  states mainly contributes around the Fermi level ( $\epsilon_F$ ) and one can see three peak structures corresponding to three crystal-field split  $p$  orbitals. The energy distribution of O  $2p$  and Zr  $4d$  states remains almost similar to that of pure ZrO<sub>2</sub>. There is a large density of unoccupied N  $2p$  states just above the  $\epsilon_F$ . This indicates that N doping is equivalent to creating holes in the system and unoccupied N  $2p$  states form an unoccupied impurity band. The width of the unoccupied impurity band is increasing with increase in N content and found to be about 0.11, 0.18 and 0.19 eV for  $x=1/32$ ,  $1/16$  and  $1/8$  compounds, respectively.

The total energy calculations of Zr<sub>4</sub>O<sub>7</sub>F in monoclinic and tetragonal structures also suggest that the monoclinic phase is a true ground state as its energy is found to be  $\sim 1634$  meV less than that of tetragonal structure. On comparing this energy difference with that of ZrO<sub>2</sub> and Zr<sub>4</sub>O<sub>7</sub>N one can say that the F-doping is providing better stability to the monoclinic structure, which is a true ground state structure for all the concentrations studied here. The TDOS of F-doped compounds are shown in Fig. 3. Contrary to the N-doped compounds the  $\epsilon_F$  of the F-doped compounds pinned at the CB which consists of Zr  $4d$  states. As opposed to N  $2p$  states crystal-field split three F  $2p$  bands contribute deep inside the VB and below 10 eV of the  $\epsilon_F$ . One may get surprised by this result as the simple picture of impurity doping in a semiconductor does

not appear to hold here. In this picture replacing some of O by F is equivalent to doping electrons in the system and one would have expected that an extra F  $2p$  electron should contribute near the bottom of the CB as an occupied impurity band. However, Zr  $4d$  electrons are found to contribute in the occupied impurity band. Here it is important to note that the simple picture of impurity doping in the semiconductor is historically based on the studies of covalent semiconductors [29]. The present system under study is an ionic semiconductor. In the case of ZrO<sub>2</sub> charge neutrality condition requires that two Zr  $4d$  electrons should be transferred to the O atoms. However, replacing O by F requires only one Zr  $4d$  electron to be transferred to F and remaining one Zr  $4d$  electron is expected to contribute in the CB in accordance with the calculated result. The width of the occupied impurity band is increasing with increase in F content and found to be about 0.12, 0.14 and 0.24 eV for  $x=1/32$ ,  $1/16$  and  $1/8$  compounds, respectively.

The present work clearly shows the  $p$ - and  $n$ -type doping when O is replaced by N and F, respectively and bandwidth of hole and electron like impurity bands can be tuned by varying the doping concentration. Thus N- and F-doped ZrO<sub>2</sub> may be used to fabricate a  $p$ - $n$  junction. Since the ZrO<sub>2</sub> is a direct band gap semiconductor and its band gap lies in the UV range, therefore, such  $p$ - $n$  junction is expected to be used in manufacturing the UV-LED. It is important to note that the light extraction in LEDs is a major research area where people are trying to get more light so that it may be useful for various purposes. Reducing the heating effect of LEDs is another important area of research. Both issues are related to the higher refractive indices of the materials conventionally used in manufacturing the LEDs. Higher the refractive index of a material separating air lower will be the critical angle of total internal reflection and hence more light will get back to the material (less will pass through the air) itself resulting in more heating of it. The refractive indices of most of the materials used in manufacturing LEDs are more than 3 [30]. However, the refractive index of ZrO<sub>2</sub> is  $\sim 2.6$  at 5 eV and expected to provide better light extraction capability in the UV range. Recently, it has been shown that UV radiation of  $\sim 265$  nm (i.e.  $\sim 4.7$  eV) acts as an effective disinfectant [31]. The bandwidths of the unoccupied and occupied impurity bands are found to be about 0.12 eV each for  $x=1/32$  N- and F-doped compounds. Further, these band gaps can further be increased by increasing the doping concentrations. Thus, one expects that radiation emitted from LED manufactured by  $p$ - $n$  junction of N- and F-doped ZrO<sub>2</sub> can be used as an effective sterilizing agent. At this juncture it is important to note that the N-doped ZrO<sub>2</sub> has already been synthesized [32] and comparison of the ionic radii of N and F with respect to O also suggests that the synthesis of F-doped ZrO<sub>2</sub> may not be a problem. In the light of these observations it is tempting to suggest that the N- and F-doped ZrO<sub>2</sub> are important  $p$ - and  $n$ -type semiconductors, respectively, that are expected to be used in making many semiconducting devices.

## 4. Conclusions

The effect of N and F doping on the electronic properties of ZrO<sub>2</sub> has been investigated by using *ab initio* electronic structure calculations. In order to find the correct band gap one needs to consider the on-site Coulomb interactions among the Zr 3*d* and O 2*p* electrons. Replacing O by N and F is found to create hole and electron like impurity states in the band gap closer to the top of the valance band and bottom of the conduction band, respectively. It is proposed that such electron and hole doped semiconductors may be used in fabricating a *p-n* junction. This *p-n* junction is expected to work as an efficient UV-LED which may be used as a disinfectant.

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## 5. Figure Captions:

Figure 1: The total density of states (TDOS) and partial density of states (PDOS) of ZrO<sub>2</sub> are shown in (a) and (b). Inset of (a) shows the evolution of band gap of ZrO<sub>2</sub> with increasing the strength of on-site Coulomb interaction ( $U$ ).

Figure 2: (Color online) Total density of states (TDOS) of ZrO<sub>2-x</sub>N<sub>x</sub> for  $x=1/32$ ,  $1/16$ , and  $x=1/8$  are shown in (a), (b), and (c), respectively.

Figure 3: (Color online) Total density of states (TDOS) of ZrO<sub>2-x</sub>F<sub>x</sub> for  $x=1/32$ ,  $1/16$ , and  $x=1/8$  are shown in (a), (b), and (c), respectively.

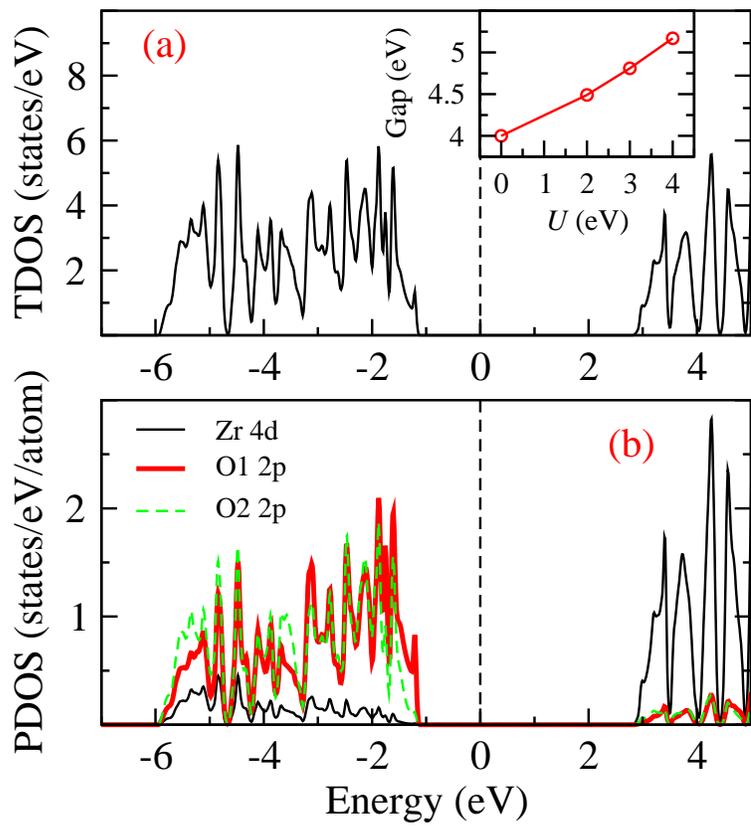


Figure 1

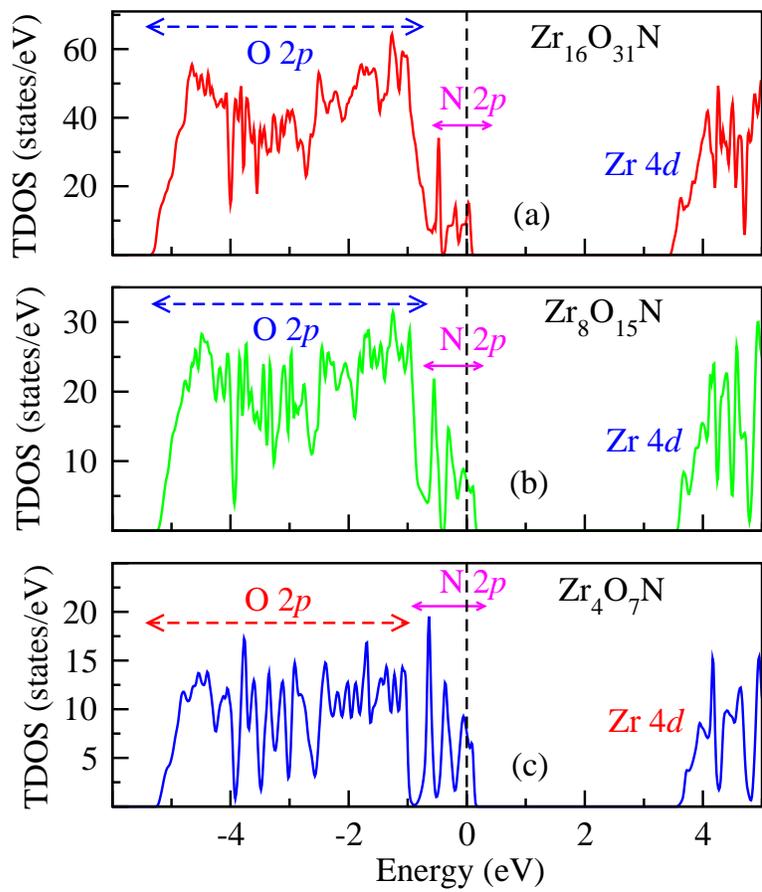


Figure 2

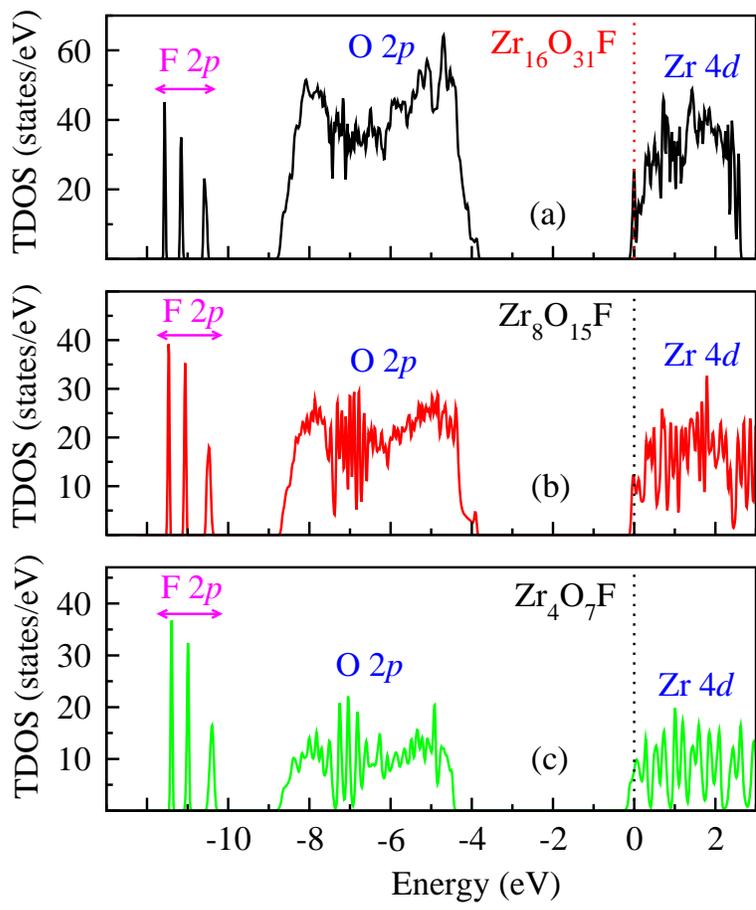


Figure 3